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Extreme Ultraviolet (EUV) Lithography IX

Kenneth A. Goldberg

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EUV: Metal-based Resists: Joint session with conferences 10583 and
10586
Jason K. Stowers, Inpria Corporation (United States)
Christopher S. Ngai, Applied Materials, Inc. (United States)

EUV Patterning I
Soichi Inoue, Toshiba Corporation (Japan)
Bryan S. Kasprovicz, Photronics, Inc. (United States)

EUV Patterning II
Yoonsuk Hyun, SK Hynix, Inc. (Korea, Republic of)
Moshe E. Preil, KLA-Tencor Corporation (United States)

RET I
Emily E. Gallagher, IMEC (Belgium)
Patrick P. Naulleau, Lawrence Berkeley National Laboratory
(United States)

EUV Optics

Jos P. Benschop, ASML Netherlands B.V. (Netherlands)

Speed Talks Poster Previews

Kenneth A. Goldberg, Lawrence Berkeley National Laboratory
(United States)

Nelson M. Felix, IBM Corporation (United States)

Patterning and Etch for EUV: Joint session with conferences 10583
And 10589

Seong-Sue Kim, SAMSUNG Electronics Company, Ltd.
(Korea, Republic of)

Richard S. Wise, Lam Research Corporation (United States)

RET II

Daniel A. Corliss, IBM Corporation (United States)

Martin Burkhardt, IBM Thomas J. Watson Research Center
(United States)

EUV Mask

Ted Liang, Intel Corporation (United States)

Emily E. Gallagher, IMEC (Belgium)

Special Session: Three Points on Shot Noise, 100 Years Later

Kenneth A. Goldberg, Lawrence Berkeley National Laboratory
(United States)

Nelson M. Felix, IBM Corporation (United States)

EUV Source

Akiyoshi Suzuki, Gigaphoton Inc. (Japan)

Kurt G. Ronse, IMEC (Belgium)

EUV Mask Defectivity

Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)

Yasin Ekinci, Paul Scherrer Institut (Switzerland)

EUV Resist Roughness

Allen H. Gabor, GLOBALFOUNDRIES Inc. (United States)

Anna Lio, Intel Corporation (United States)

Novel EUV Resist Concepts

Robert L. Brainard, SUNY CNSE/SUNYIT (United States)

Florian Gstrein, Intel Corporation (United States)